

Description

The 5N10-HXY uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

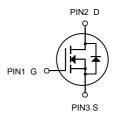


General Features

 $V_{DS} = 100V I_{D} = 5A$

 $R_{DS(ON)}$ < 120m Ω @ V_{GS} =10V

 $R_{DS(ON)} < 143 m\Omega$ @ $V_{GS}=4.5V$



Application

Battery protection

Load switch

Uninterruptible power supply

N-Channel MOSFET

Package Marking and Ordering Information

	Product ID	Pack	Marking	Qty(PCS)
Ī	5N10-HXY	SOT23-3L	1005	3000

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
VDS	DS Drain-Source Voltage		V	
VGS	VGS Gate-Source Voltage		V	
lD	I _D Drain Current-Continuous		А	
IDM	IDM Drain Current-Pulsed (Note 1)		Α	
P _D	P _D Maximum Power Dissipation		W	
TJ,TSTG	TJ,TSTG Operating Junction and Storage Temperature Range		$^{\circ}$	
RθJA	RθJA Thermal Resistance,Junction-to-Ambient (Note 2)		°C/W	



Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	100	-	-	V
Zero Gate Voltage Drain Current	IDSS	V _{DS} =100V,V _{GS} =0V	_	-	1	μΑ
Gate-Body Leakage Current	Igss	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	VGS(th)	V _{DS} =V _{GS} ,I _D =250µA	1.0	1.5	2.0	V
		V _{GS} =10V, I _D =3A	-	100	120	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =4.5V, I _D =3A	-	130	143	
Forward Transconductance	g FS	V_{DS} =5 V , I_{D} =3 A	-	5	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	650	-	PF
Output Capacitance	Coss	V _{DS} =50V,V _{GS} =0V,	-	24	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	_	20	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t̄d(on)		-	6	=	nS
Turn-on Rise Time	tr	V_{DD} =50V, R_L =19 Ω	-	4	-	nS
Turn-Off Delay Time	td(off)	V_{GS} =10 V , R_{G} =3 Ω	-	20	-	nS
Turn-Off Fall Time	tf		_	4	-	nS
Total Gate Charge	Qg		-	20		nC
Gate-Source Charge	Qgs	V_{DS} =50V, I_D =3A, V_{GS} =10V	-	2.1	-	nC
Gate-Drain Charge	Q _{gd}		-	3.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V,I _S =3A	-	=	1.2	V
Diode Forward Current (Note 2)	Is		_	_	3	Α

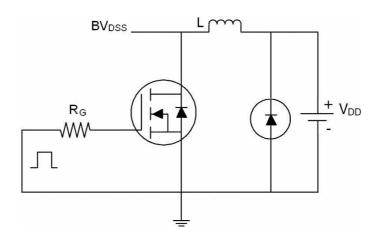
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width ≤ 300μ s, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production

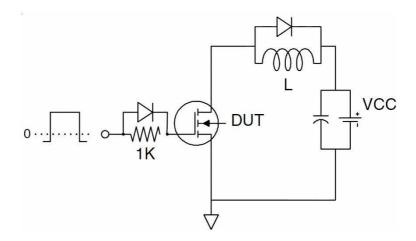


Test Circuit

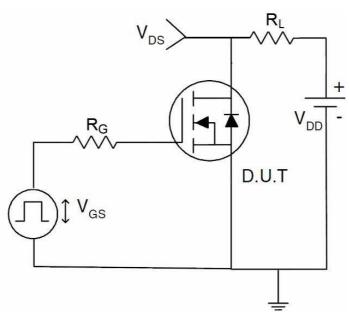
1) E_{AS} test circuit



2) Gate charge test circuit



3) Switch Time Test Circuit





Typical Electrical and Thermal Characteristics (Curves)

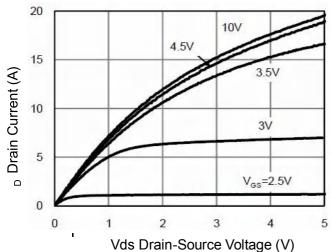


Figure 1 Output Characteristics

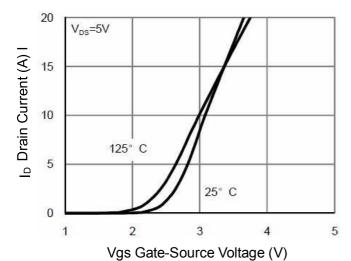
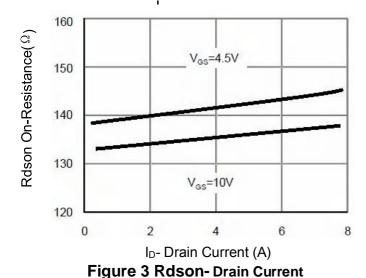


Figure 2 Transfer Characteristics



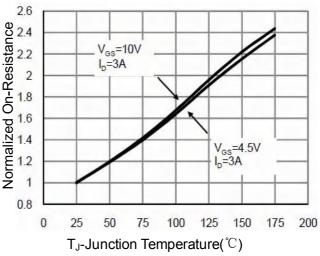


Figure 4 Rdson-JunctionTemperature

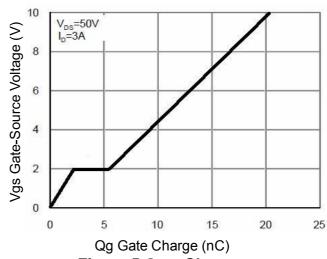


Figure 5 Gate Charge

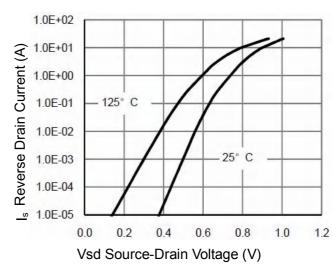


Figure 6 Source- Drain Diode Forward

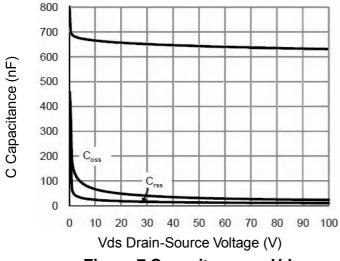


Figure 7 Capacitance vs Vds

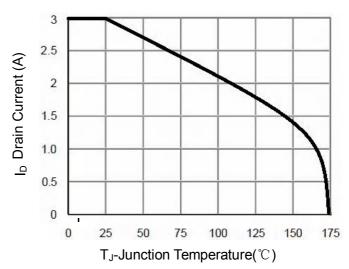


Figure 9 BV_{DSS} vs Junction Temperature

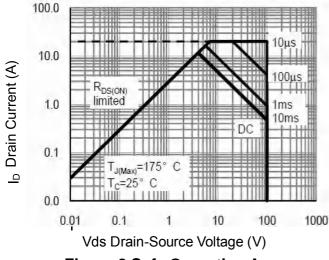


Figure 8 Safe Operation Area

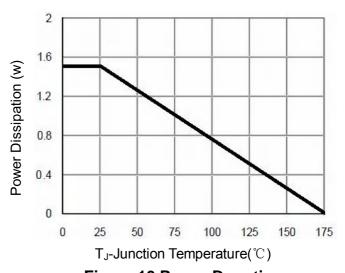
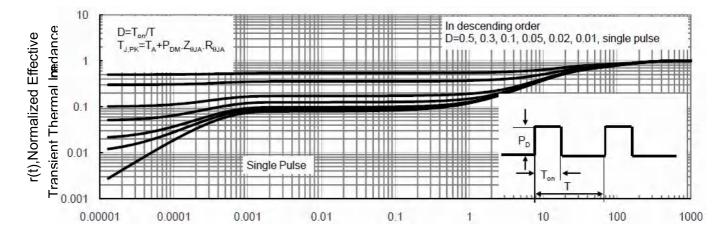


Figure 10 Power De-rating

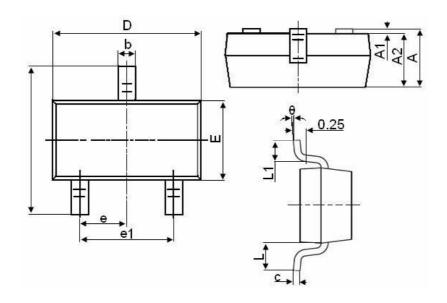


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



SOT23-3L Package Information



	Dimensions in Millimeters			
Symbol	MIN.	MAX.		
А	1.050	1.250		
A1	0.000	0.100		
A2	1.050	1.150		
b	0.300	0.500		
С	0.100	0.200		
D	2.800	3.000		
E	1.500	1.700		
E1	2.650	2.950		
е		0.950TYP		
e1	1.800	2.000		
L		0.550REF		
L1	0.300	0.600		
θ	0°	8°		



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